

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L8	1152	(257/510 or 257/513).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:40
L9	1397	(257/647 or 257/659).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:49
L10	575	(257/395-397).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
L11	216	semiconductor and (((trench\$4 or recess\$4 or groove or STI) with ((liner or layer) near7 (top or above or over))) same ((nitride or SiN) with (cvd or (vapor adj deposit\$\$\$))) and (((High adj density) near3 plasma) or HDP)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:03
L12	60	semiconductor and (((trench\$4 or recess\$4 or groove or STI) with ((liner) near7 (top or above or over))) same (HDP or ((high adj density) near3 plasma)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/09/19 13:41